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Sheet 1 of 1

Complete If Known	
Application Number	~~TBA~~ 10/617737
Filing Date	Herewith
First Named Inventor	Takashi OHSAWA
Group Art Unit	~~Unknown~~ 2815
Examiner Name	~~Unknown~~ A. Wilson
Attorney Docket Number	002372.00045

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Examiner Signature	A. Wilson	Date Considered	9/2/04

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